



# STB14NF10 STP14NF10 - STP14NF10FP

N-channel 100V - 0.115Ω - 15A - D<sup>2</sup>PAK/TO-220/TO-220FP  
Low gate charge STripFET™ II Power MOSFET

## General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STB14NF10	100V	<0.13Ω	15A
STP14NF10	100V	<0.13Ω	15A
STP14NF10	100V	<0.13Ω	15A

- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

## Description

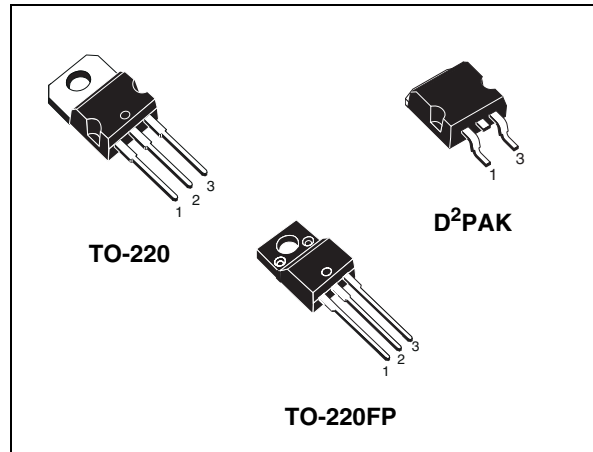
This MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

## Applications

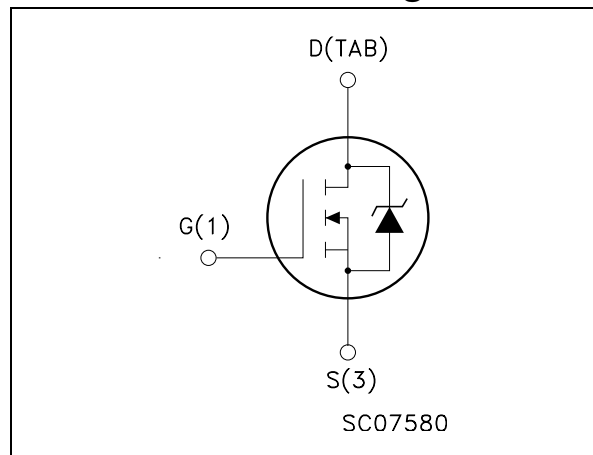
- Switching application

## Order codes

Part number	Marking	Package	Packaging
STB14NF10T4	B14NF10	D <sup>2</sup> PAK	Tape & reel
STP14NF10	P14NF10	TO-220	Tube
STP14NF10FP	P14NF10FP	TO-220FP	Tube



## Internal schematic diagram



# Contents

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# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		D <sup>2</sup> PAK TO-220	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	100		V
V <sub>DGR</sub>	Drain-gate voltage (R <sub>GS</sub> = 20 kΩ)	100		V
V <sub>GS</sub>	Gate- source voltage	± 20		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25°C	15	10	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100°C	10	6.3	A
I <sub>DM</sub> <sup>(1)</sup>	Drain current (pulsed)	60	40	A
P <sub>tot</sub>	Total dissipation at T <sub>C</sub> = 25°C	60	25	W
	Derating Factor	0.4	0.17	W/°C
dv/dt <sup>(2)</sup>	Peak diode recovery voltage slope	9		V/ns
E <sub>AS</sub> <sup>(3)</sup>	Single pulse avalanche energy	70		mJ
V <sub>ISO</sub>	Insulation withstand voltage (DC)	--	2500	V
T <sub>stg</sub>	Storage temperature	-55 to 175		°C
T <sub>j</sub>	Max. operating junction temperature			

1. Pulse width limited by safe operating area.
2. I<sub>SD</sub> ≤ 4A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>
3. Starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 15A, V<sub>DD</sub> = 50V

**Table 2. Thermal data**

	Parameter	D <sup>2</sup> PAK TO-220	TO-220FP	Unit
		R <sub>thj-case</sub>	Thermal resistance junction-case max	
R <sub>thj-amb</sub>	Thermal resistance junction-ambient max	62.5		°C/W
T <sub>J</sub>	Maximum lead temperature for soldering purpose	300		°C

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	100			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max ratings}$ $V_{DS} = \text{max ratings},$ $T_C = 125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20V$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 7A$		0.115	0.13	$\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 7A$		20		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		460 70 30		pF pF pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 50V, I_D = 7A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see <a href="#">Figure 15</a> )		16 25 32 8		ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 80V, I_D = 12A,$ $V_{GS} = 10V$ (see <a href="#">Figure 16</a> )		15.5 3.7 4.7	21	nC nC nC

1. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %.

**Table 5. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)				15 60	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 14A, V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 14A,$ $di/dt = 100A/\mu s,$ $V_{DD} = 50V, T_j = 150^\circ C$ (see <a href="#">Figure 17</a> )		90 230 5		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/D<sup>2</sup>PAK

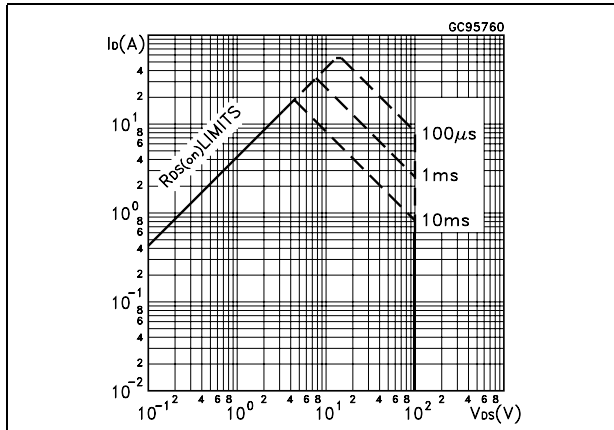


Figure 2. Thermal impedance for TO-220/D<sup>2</sup>PAK

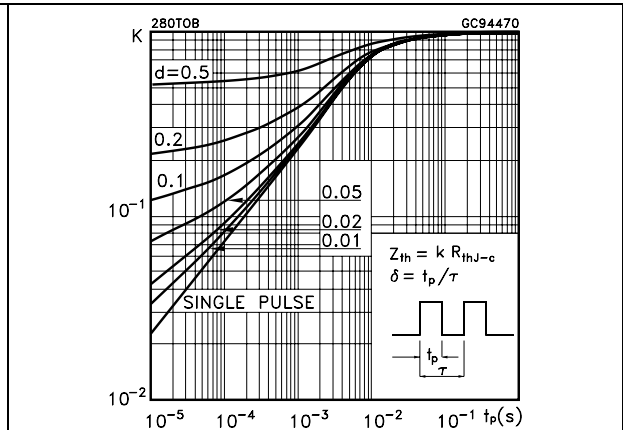


Figure 3. Safe operating area for TO-220FP

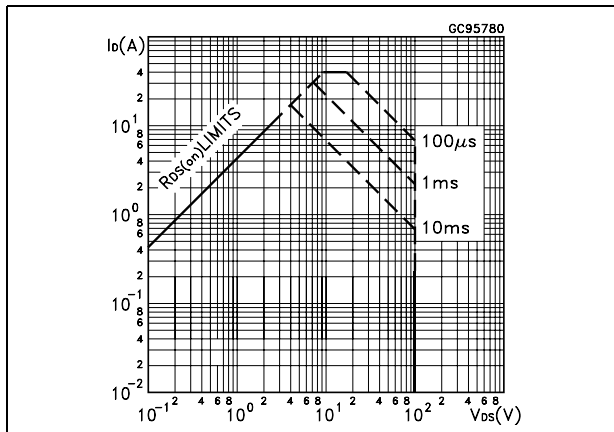


Figure 4. Thermal impedance for TO-220FP

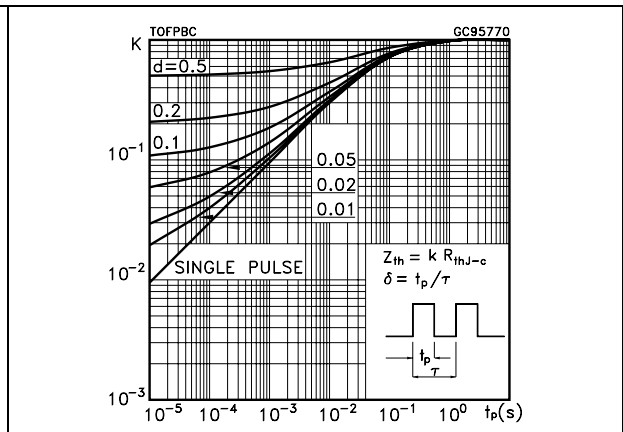


Figure 5. Output characteristics

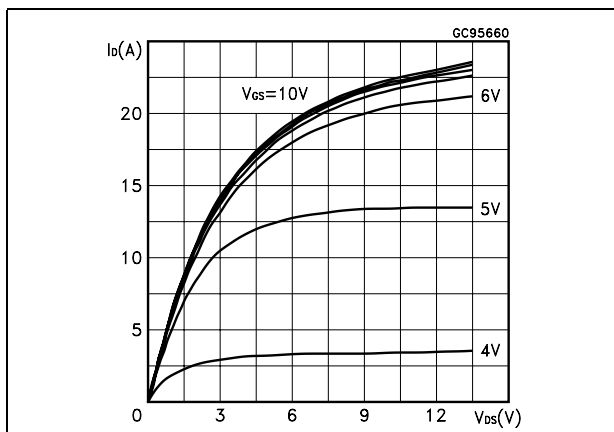


Figure 6. Transfer characteristics

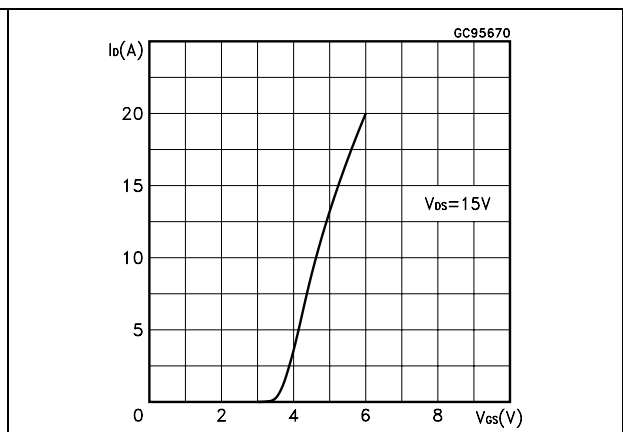


Figure 7. Transconductance

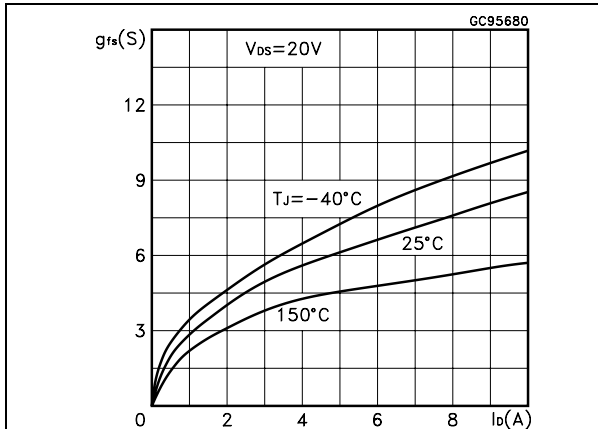


Figure 8. Static drain-source on resistance

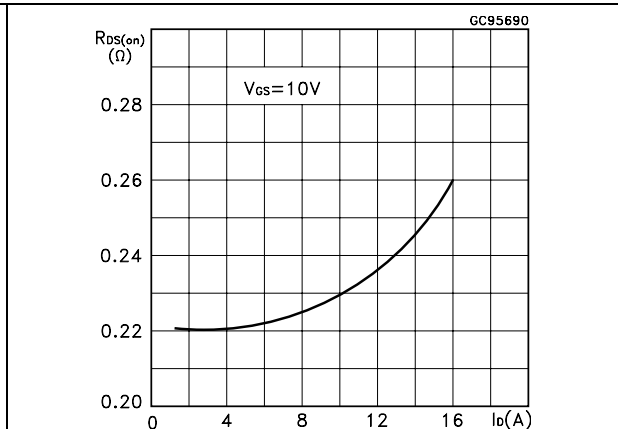


Figure 9. Gate charge vs gate-source voltage

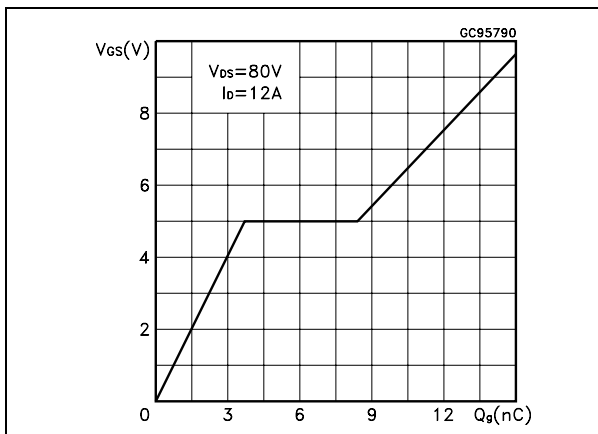


Figure 10. Capacitance variations

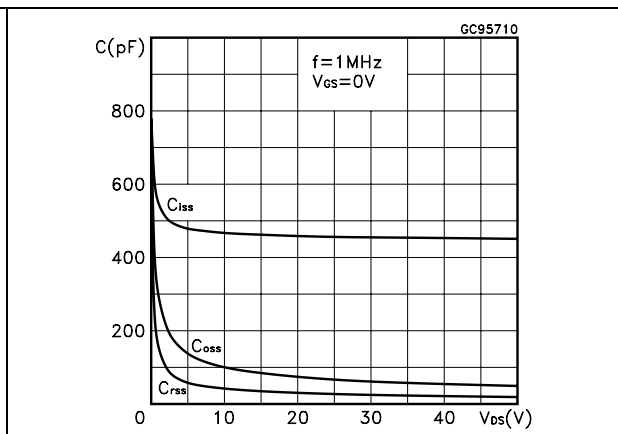


Figure 11. Normalized gate threshold voltage vs temperature

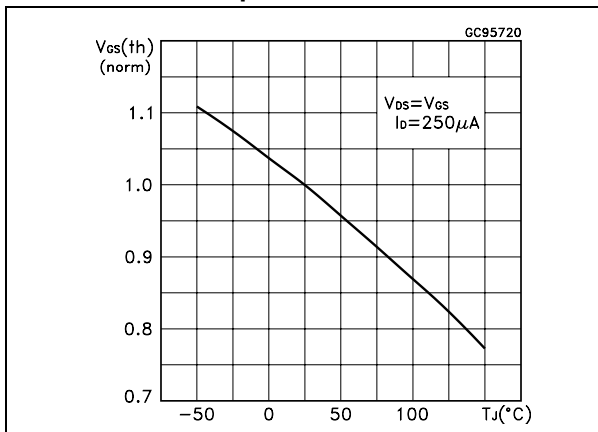


Figure 12. Normalized on resistance vs temperature

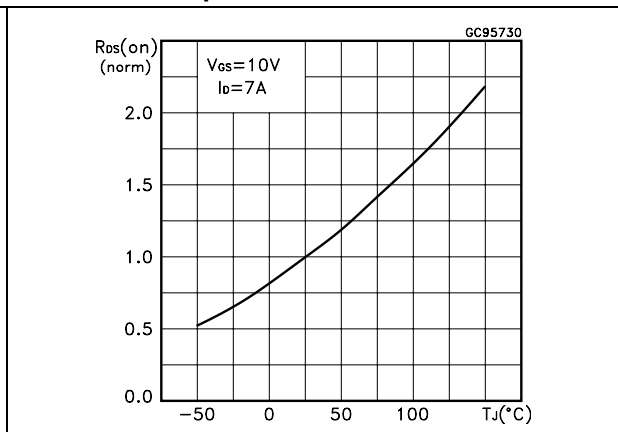


Figure 13. Source-drain diode forward characteristics

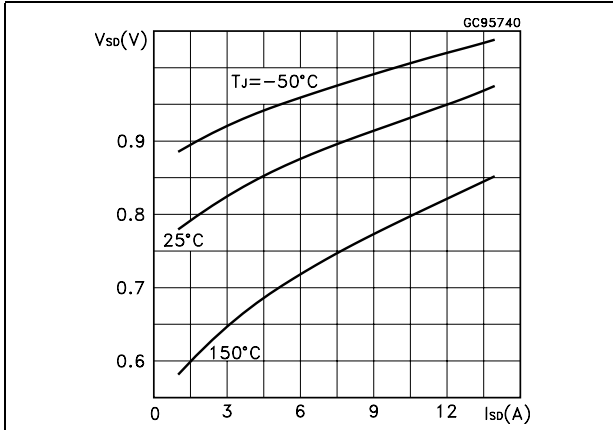
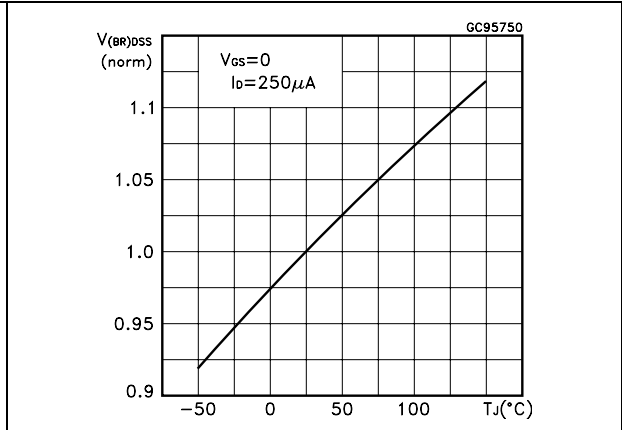


Figure 14. Normalized  $B_{VDSS}$  vs temperature





### 3 Test circuit

Figure 15. Switching times test circuit for resistive load



Figure 16. Gate charge test circuit



Figure 17. Test circuit for inductive load switching and diode recovery times



Figure 18. Unclamped Inductive load test circuit



Figure 19. Unclamped inductive waveform



Figure 20. Switching time waveform

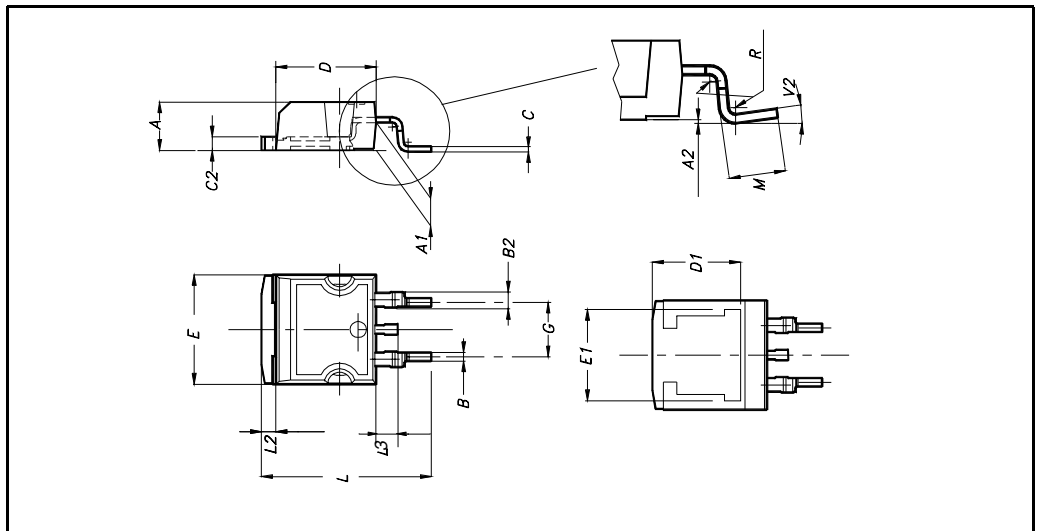


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

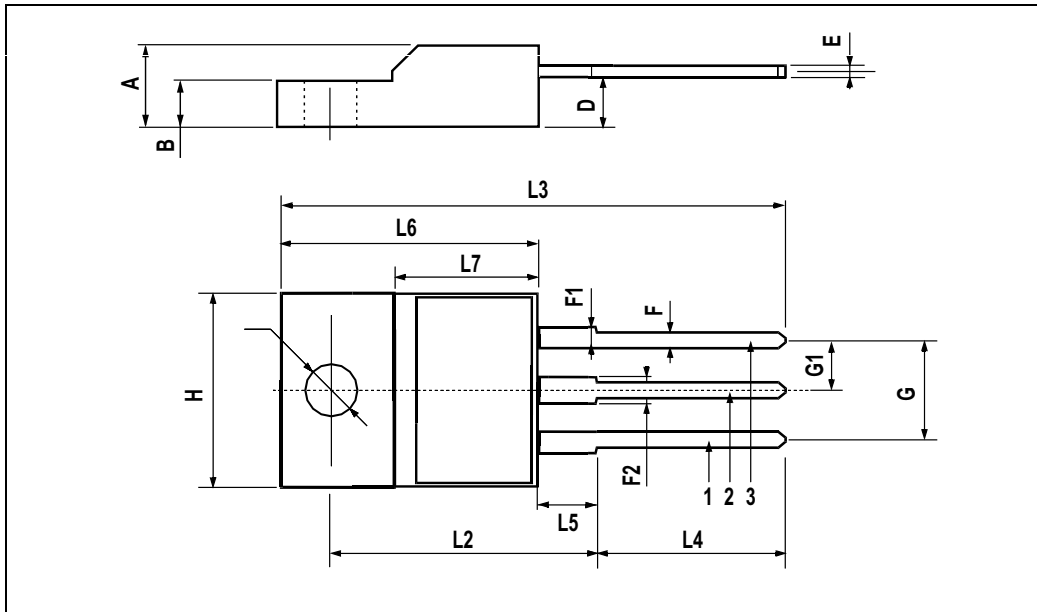
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



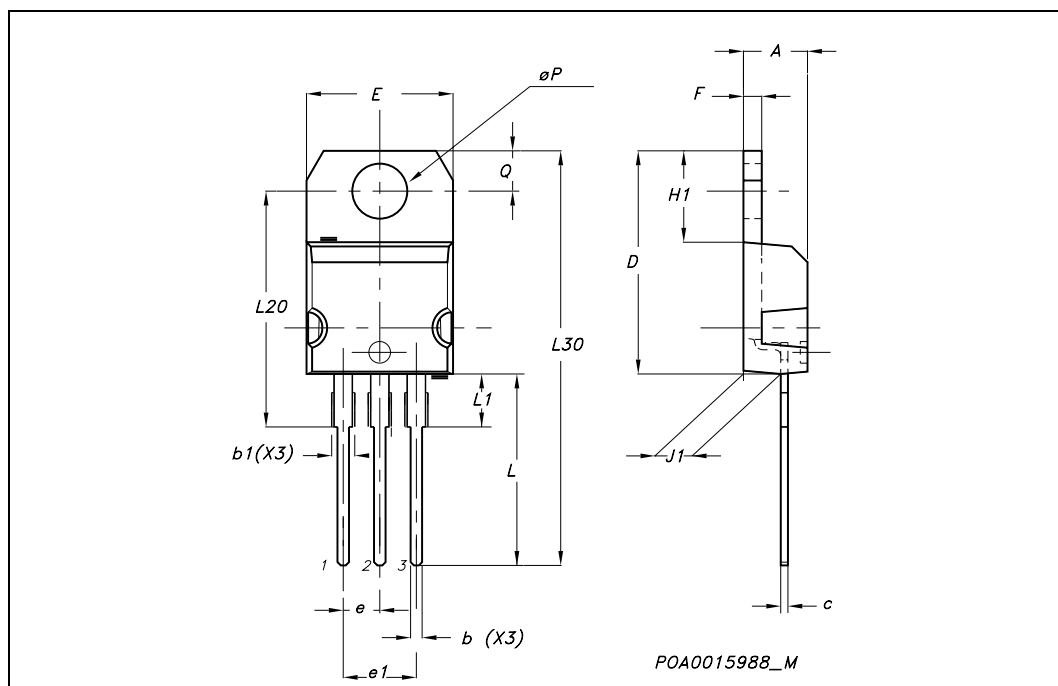
**TO-220FP MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



## TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

**TRL**

FEED DIRECTION

Bending radius R min.

\* on sales type

## 6 Revision history

**Table 6. Revision history**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
05-Feb-2004	1	First version
21-Jun-2004	2	Preliminary version
19-Jun-2006	3	New template, no content change

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